

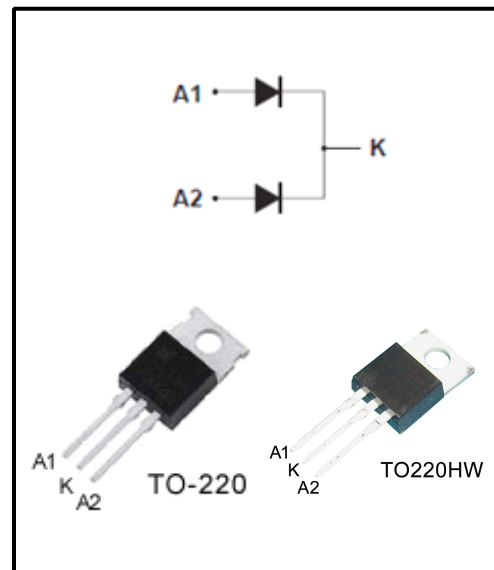
**Power Schottky Rectifier**

**Features**

- 20A(2×10A),100V
- $V_F(\text{max})=0.7\text{V}(@T_J=125^\circ\text{C})$
- Low power loss, high efficiency
- Common cathode structure
- Guard ring for over voltage protection, High reliability
- Maximum Junction Temperature Range(175°C)

**General Description**

Dual center tap Schottky rectifiers suited for High frequency switch power supply and Free wheeling diodes, polarity protection applications.



**Absolute Maximum Ratings**

Symbol	Parameter	Value	Units
$V_{\text{DRM}}$	Repetitive peak reverse voltage	100	V
$V_{\text{DC}}$	Maximum DC blocking voltage	100	V
$I_{\text{F(AV)}}$	Average forward current	per diode	10
		per device	20
$I_{\text{FSM}}$	Surge non repetitive forward current	200	A
$T_{\text{J}}$	Junction Temperature	175	°C
$T_{\text{stg}}$	Storage Temperature	-40~150	°C

**Thermal Characteristics**

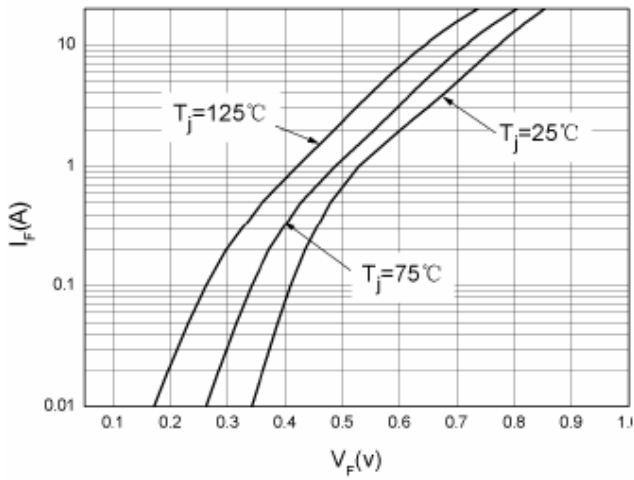
Symbol	Parameter	Value			Units
		Min	Typ	Max	
$R_{\text{QJC}}$	Thermal Resistance, Junction-to-Case	-	-	1.9	°C/W

**Ordering Information**

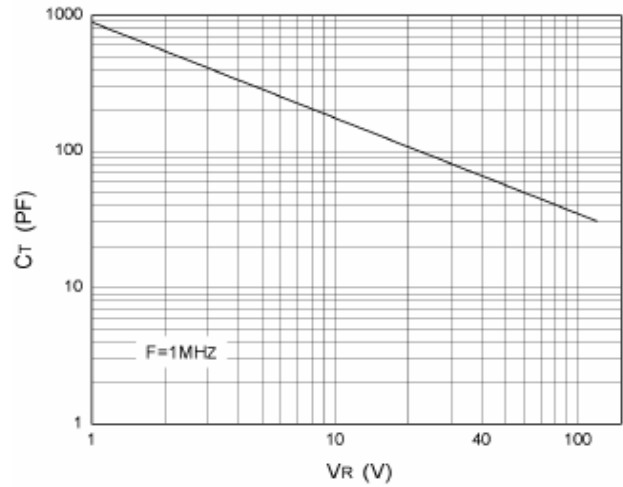
Order codes	Package	Marking	Halogen Free	Packaging
WSP20D100L	TO220C	P20D100L	NO	Tube
WSP20D100-HW	TO220HW	P20D100	NO	Tube

## Electrical Characteristics (per diode)

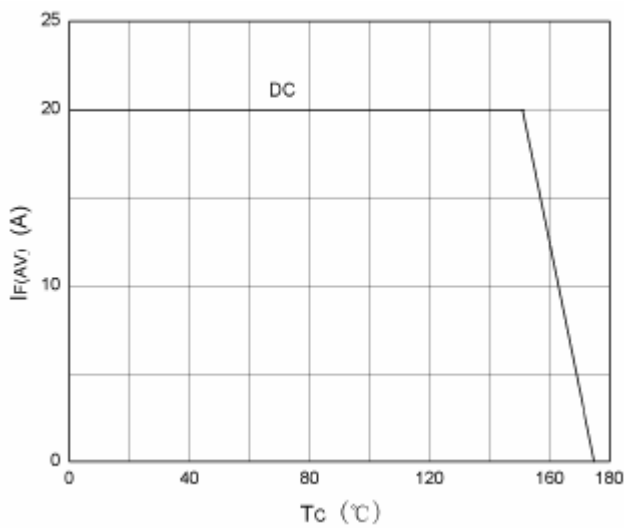
Characteristics	Symbol	Test Condition		Min	Typ.	Max	Unit
Reverse leakage current	$I_R$	VR = VRRM	Tj = 25°C	-	-	10	$\mu$ A
			Tj = 125°C		-	5	mA
Forward voltage drop	$V_F$	IF= 10A	Tj = 25°C	-	0.78	0.85	V
			Tj = 125°C	-	0.65	0.7	



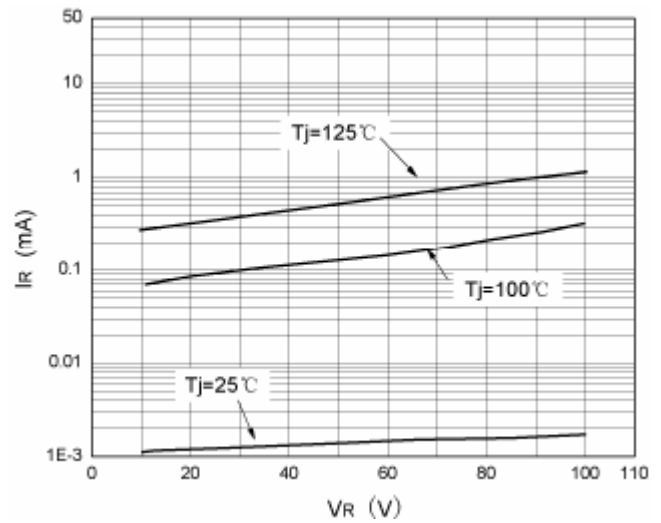
**Fig.1 Forward voltage drop versus forward current (maximum values, per diode).**



**Fig.2 Junction capacitance versus reverse voltage applied (typical values, per diode).**

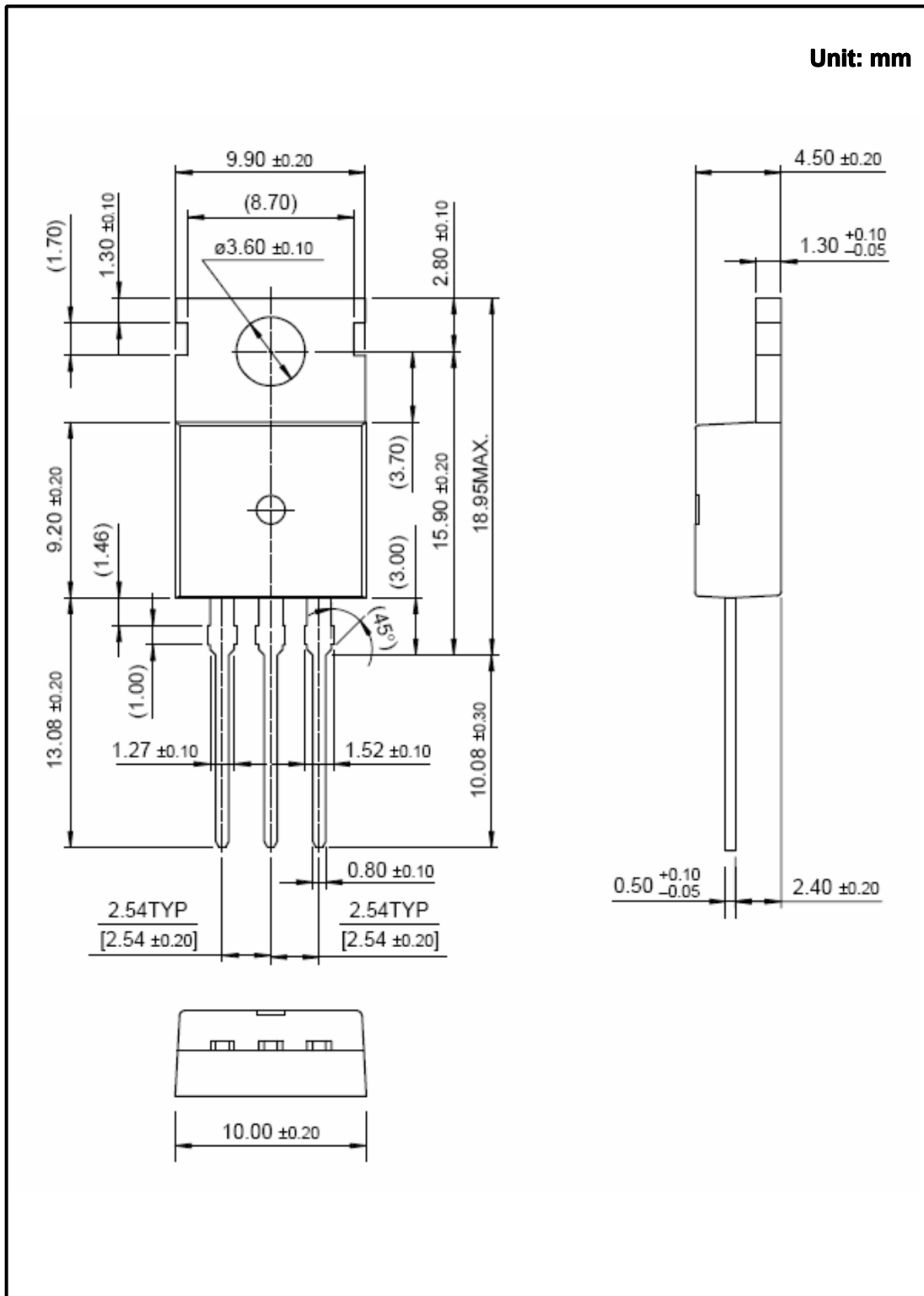


**Fig.3 Average current versus ambient temperature ( $d=0.5$ ) (per diode)**



**Fig.4 Reverse leakage current versus reverse voltage applied (typical values, per diode)..**

**TO-220 Package Dimension**



**TO-220HW Package Dimension**

